

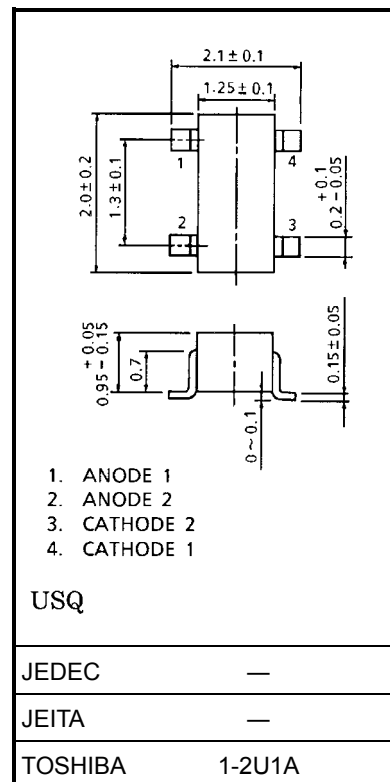
TOSHIBA DIODE Silicon Epitaxial Planar Type

JDV4P08U

VCO for UHF Band Radio

Unit: mm

- High Capacitance Ratio: $C_{1V}/C_{4V} = 3.0$ (typ.)
- Low Series Resistance : $r_s = 0.35 \Omega$ (typ.)
- The device incorporates two diodes which have no common pins, and is suitable for high-density mounting.



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

Weight: g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu A$	10	—	—	V
Reverse current	I_R	$V_R = 10 V$	—	—	3	nA
Capacitance	C_{1V}	$V_R = 1 V, f = 1 MHz$	17.3	18.3	19.3	pF
	C_{4V}	$V_R = 4 V, f = 1 MHz$	5.3	6.1	6.6	
Capacitance ratio	C_{1V}/C_{4V}	—	2.8	3.0	—	—
Series resistance	r_s	$V_R = 1 V, f = 470 MHz$	—	0.35	0.5	Ω

Note: Signal level when capacitance is measured: $V_{sig} = 500 mV_{rms}$

Marking